
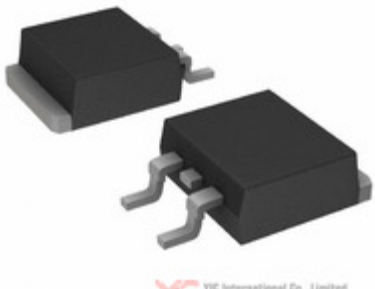










	<p>SUD35N10-26P-GE3</p>
	<p>Hersteller-Teilenummer: SUD35N10-26P-GE3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET N-CH 100V 35A DPAK</p> <p>Datenblätter:  SUD35N10-26P-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 23500 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SUD35N10-26P-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET N-CH 100V 35A DPAK
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	23500 pcs Stock
Hersteller Standard Vorlaufzeit	33 Weeks
detaillierte Beschreibung	N-Channel 100V 35A (Tc) 8.3W (Ta), 83W (Tc) Surface
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 175°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-252-3, DPak (2 Leads + Tab), SC-63
Supplier Device-Gehäuse	TO-252, (D-Pak)
Verlustleistung (max)	8.3W (Ta), 83W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	100V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	35A (Tc)
Rds On (Max) @ Id, Vgs	26 mOhm @ 12A, 10V
VGS (th) (Max) @ Id	4.4V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	47nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	2000pF @ 12V
Antriebsspannung (Max Rds On, Min Rds On)	7V, 10V
Vgs (Max)	±20V
Verpackung	Cut Tape (CT)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SUD35N10-26P-GE3CT

SUD35N10-26P-GE3 ist neu im Original, Suche SUD35N10-26P-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SUD35N10-26P-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SUD35N10-26P-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SUD35N10-26P-T4GE3 Vishay / Siliconix MOSFET N-CH 100V 35A TO252</p>	 <p>SUD35N05-26L-E3 Electro-Films (EFI) / Vishay MOSFET N-CH 55V 35A TO252</p>	 <p>SUD35N05-26L-E3 Vishay / Siliconix MOSFET N-CH 55V 35A TO252</p>	 <p>SUD35N10-26P-GE3 Vishay / Siliconix MOSFET N-CH 100V 35A DPAK</p>
 <p>SUD35N10-26P-E3 Vishay / Siliconix MOSFET N-CH 100V 35A TO252</p>	 <p>SUD40N02-08-E3 Vishay / Siliconix MOSFET N-CH 20V 40A TO252</p>	 <p>SUD35N10-26P Vishay SUD35N10-26P Vishay</p>	 <p>SUD40151EL-GE3 Electro-Films (EFI) / Vishay MOSFET P-CHAN 40V TO-252</p>

heiße Teile

Mehr

⊛ SUD23N06-31L-GE3	↔ SUD23N06-31L-T1-E3	⇒ SUD23N06-31_08	D SUD23N06-31_11	⇒ SUD25N04-25
⊣ SUD25N04-25-T4-E3	⊛ SUD25N04-25-T4-E3	D SUD25N05-13L	⇒ SUD25N05-45L	⇒ SUD25N06-45L
⊛ SUD25N06-45L-E3	⊣ SUD25N06-45L-GE3	⊛ SUD25N15-52	↔ SUD25N15-52-E3	⇒ SUD25N15-52-E3
D SUD30N03-30	⊛ SUD30N04-10	⊣ SUD30N04-10-E3	⊛ SUD30N06-30	⇒ SUD35N05-26L
⇒ SUD35N05-26L-E3	↔ SUD35N05-26L-E3	⊛ SUD35N10-26P	⊣ SUD35N10-26P-E3	⇒ SUD35N10-26P-E3
↔ SUD35N10-26P-GE3	⇒ SUD40N02-08-E3	D SUD40N02-08-E3	⊛ SUD40N02-3M3P	⊣ SUD40N02-3M3P-E3
⊛ SUD40N02-3M3P-E3	D SUD40N03-18P	⇒ SUD40N03-18P-E3	↔ SUD40N04	⇒ SUD40N04-10A
⊣ SUD40N04-10A-E3	⊛ SUD40N04-10A-E3	↔ SUD40N04-20	⇒ SUD40N06-25L	⇒ SUD40N08-16
⊛ SUD40N08-16-E3	⊣ SUD40N08-16-E3	⊛ SUD40N08-16-E3.	D SUD40N08-16-T4-E3	⇒ SUD40N08-16_08
↔ SUD40N10-25	⊛ SUD40N10-25-E3	⊣ SUD40N10-25-E3	⊛ SUD40P03-20	⇒ SUD42N03-3M9P

Contact us:Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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